



100V N-Channel SGT Power MOSFET

General Description

The SJH049N10 uses SGT technology to provide excellent $R_{DS(ON)}$, low gate charge and fast switching characteristics. This device is suitable for use as a wide variety of applications.

Features

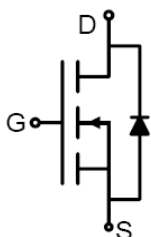
- Low Gate Charge
- 100% UIS Tested, 100% DVDS Tested
- High Power and current handing capability
- Lead free product is acquired

Application

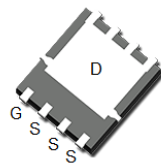
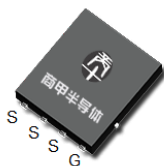
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

Key Performance Parametes

Parameter	Value	Unit
V_{DS}	100	V
$R_{DS(ON_TYP)}$	4.2	$m\Omega$
I_D	93	A
Q_G	55	nC



Schematic Diagram



PDFN5X6-8L top&bottom view



Package Marking and Ordering Information

Device/Ordering Code	Marking	Package	Packing	Reel Size	Tape width	Quantity
SJH049N10	SJH049N10	PDFN5X6	Tape	\	\	5000 Pcs

Table 1. Absolute Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage ($V_{GS}=0V$)	100	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0V$)	± 20	V
I_D	Drain Current-Continuous($T_c=25^\circ\text{C}$)	93	A
	Drain Current-Continuous($T_c=100^\circ\text{C}$)	59	A
$I_{DM}(\text{pluse})$	Drain Current-Continuous@ Current-Pulsed (Note 1)	372	A
P_D	Maximum Power Dissipation($T_c=25^\circ\text{C}$)	89	W
	Maximum Power Dissipation($T_c=100^\circ\text{C}$)	36	W
E_{AS}	Avalanche energy (Note 2)	506	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ\text{C}$

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
R_{JC}	Thermal Resistance, Junction-to-Case		1.4	$^\circ\text{C}/\text{W}$



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Table 3. Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =250μA	100			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} =0V T _J =25°C			1	μA
		V _{DS} =100V, V _{GS} =0V T _J =125°C			100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	2		4	V
g _{FS}	Forward Transconductance	V _{DS} =10V, I _D =20A		34		S
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =20A T _J =25°C		4.2	5.5	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =50V, V _{GS} =0V, f=1.0MHz		3450		pF
C _{oss}	Output Capacitance			855		pF
C _{rss}	Reverse Transfer Capacitance			23		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1.0MHz		1.6		Ω
Switching Parameters						
t _{d(on)}	Turn-on Delay Time	V _{GS} =10V, V _{DS} =50V, R _L =2.5Ω, R _{GEN} =6Ω		40		nS
t _r	Turn-on Rise Time			28.5		nS
t _{d(off)}	Turn-Off Delay Time			61		nS
t _f	Turn-Off Fall Time			98		nS
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =50V, I _D =20A		55		nC
Q _{gs}	Gate-Source Charge			17		nC
Q _{gd}	Gate-Drain Charge			15.5		nC
Source-Drain Diode Characteristics						
I _{SD}	Source-Drain Current (Body Diode)				93	A
V _{SD}	Forward on Voltage (Note 3)	V _{GS} =0V, I _S =20A			1.2	V
t _{rr}	Reverse Recovery Time	I _F =20A, dI/dt=100A/ s		86		ns
Q _{rr}	Reverse Recovery Charge	I _F =20A, dI/dt=100A/ s		22		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

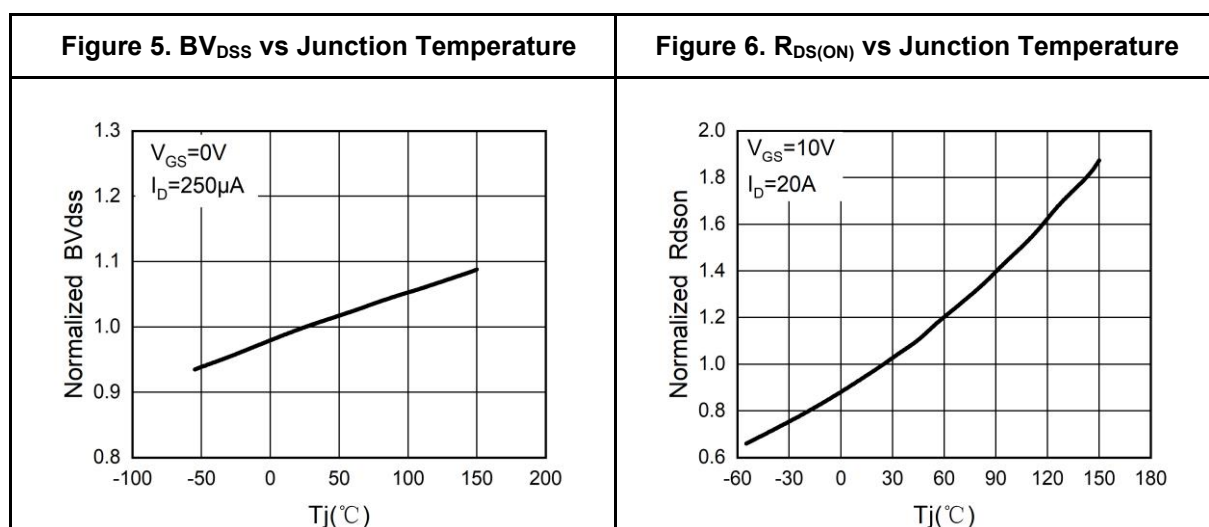
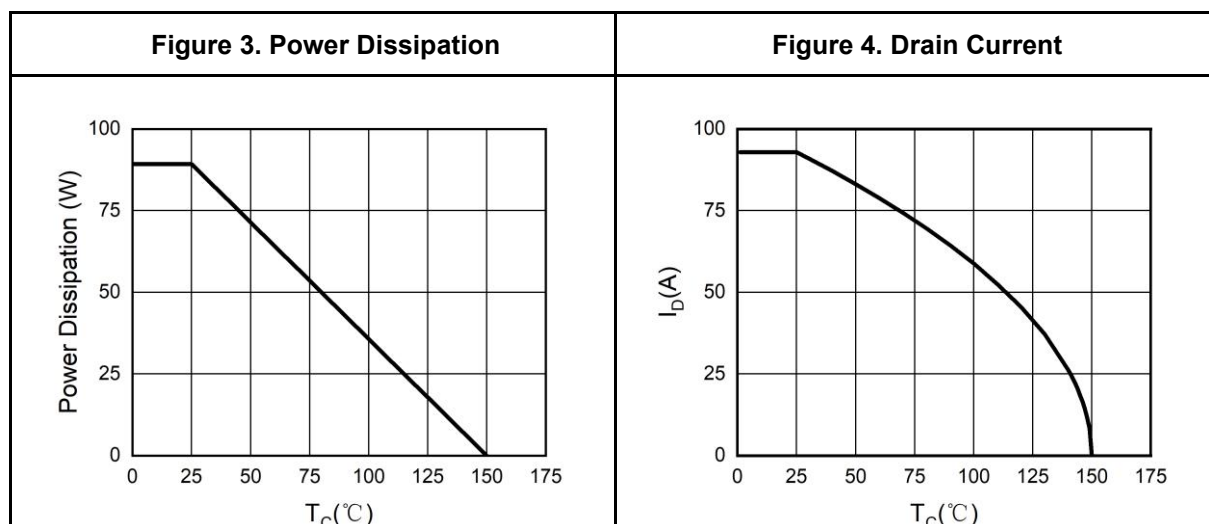
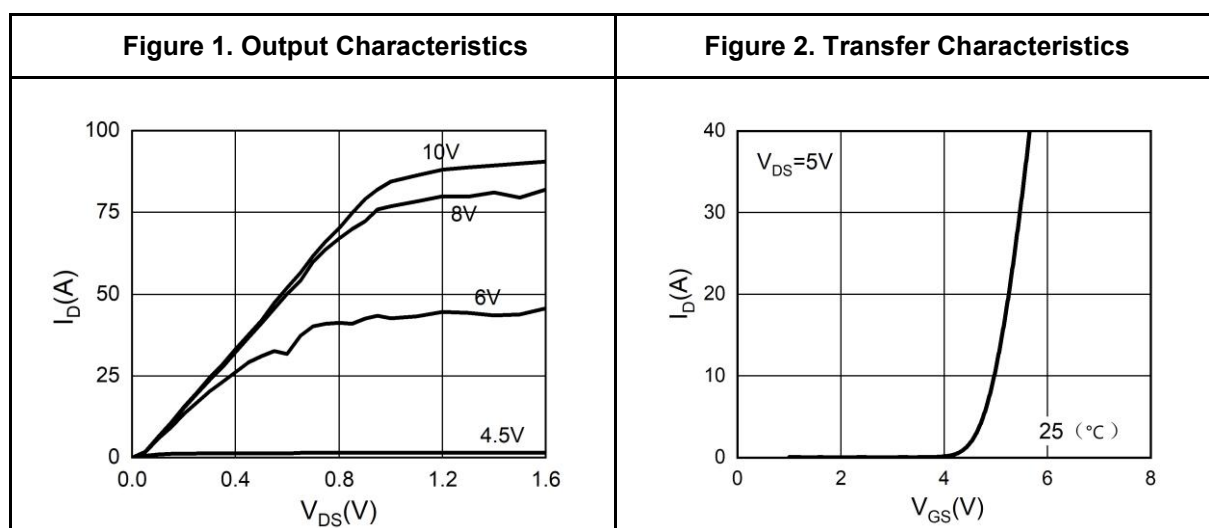
Notes 2.EAS condition: $T_J=25^{\circ}\text{C}, V_{DD}=100V, V_G=10V, R_g=25\Omega, L=0.5\text{mH}$.

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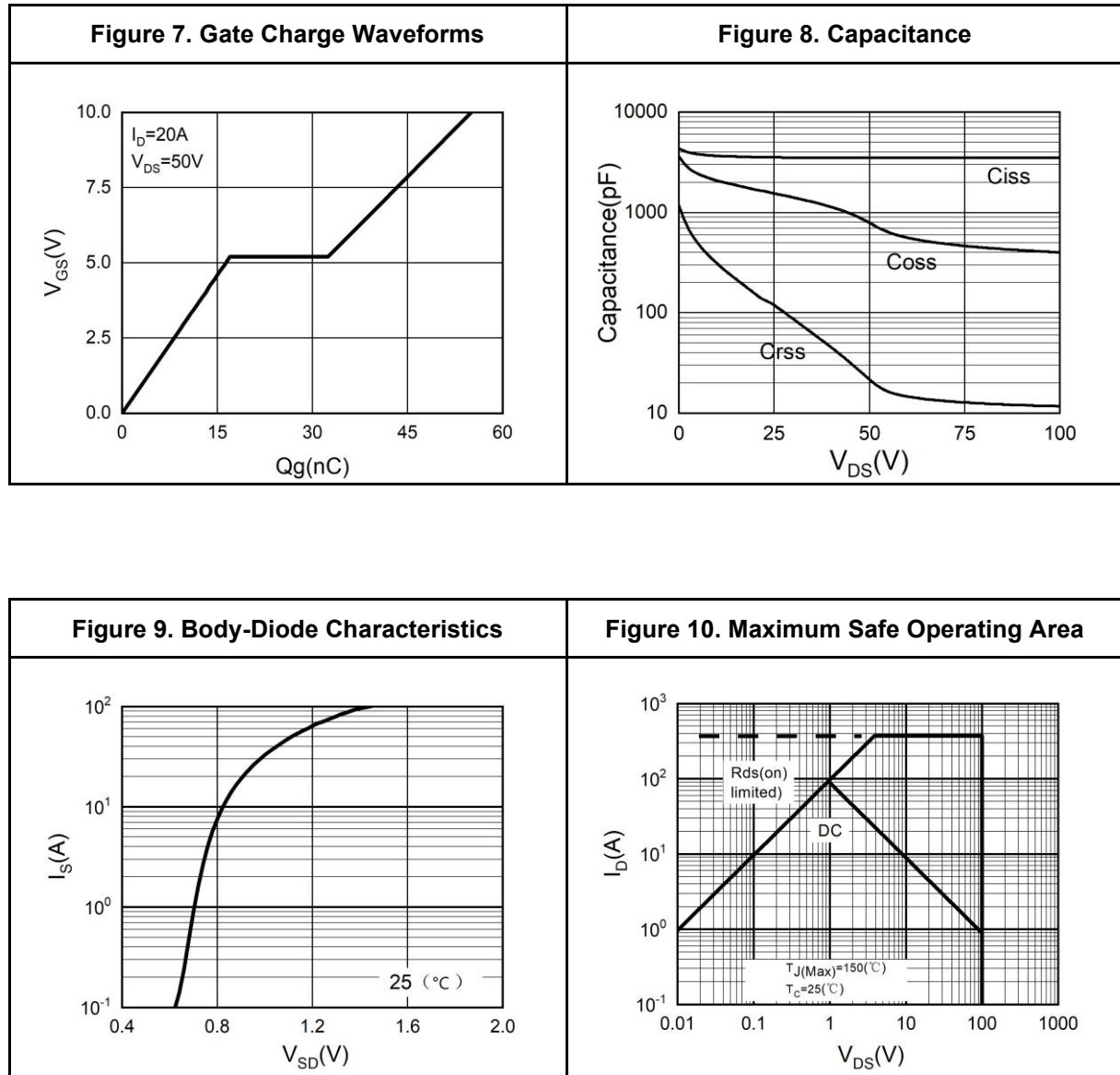
Typical Electrical And Thermal Characteristics (Curves)





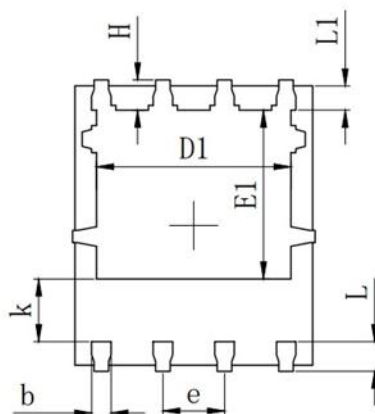
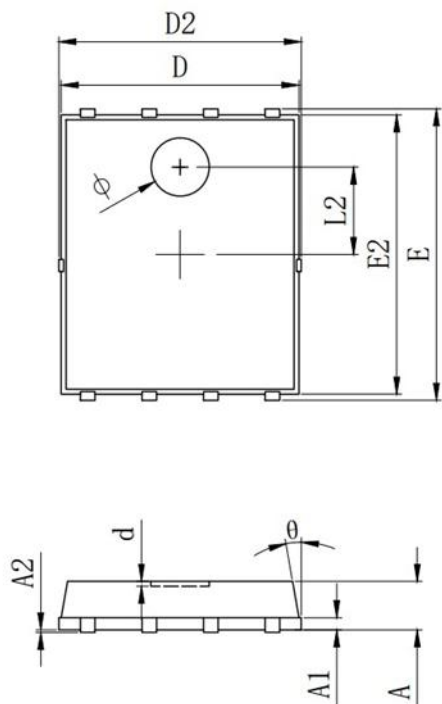
100V N-Channel SGT Power MOSFET

Typical Electrical And Thermal Characteristics (Curves)





PDFN5X6-8L Package Information



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	0.900	1.000	1.100
A1	0.254 REF.		
A2	0~0.05		
D	4.824	4.900	4.976
D1	3.910	4.010	4.110
D2	4.924	5.000	5.076
E	5.924	6.000	6.076
E1	3.375	3.475	3.575
E2	5.674	5.750	5.826
b	0.350	0.400	0.450
e	1.270 TYP.		
L	0.534	0.610	0.686
L1	0.424	0.500	0.576
L2	1.800 REF.		
k	1.190	1.290	1.390
H	0.549	0.625	0.701
θ	8°	10°	12°
Φ	1.100	1.200	1.300
d			0.100

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